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# **Analytical Techniques for Semiconductor Materials and Process Characterization 6 (ALTECH 2009)**

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## Table of Contents

Preface	iii
<b>Chapter 1</b>	
<b>Defects and Impurities</b>	
Defect Analysis in Solar Cell Silicon by Photoluminescence Spectroscopy and Topography <i>M. Tajima and H. Sugimoto</i>	3
New Modes of Fast Fourier Impedance Spectroscopy Applied to Solar Materials Characterization and Semiconductor Pore Etching <i>J. Carstensen and H. Foell</i>	11
Advanced Application of Resistivity and Hall Effect Measurements to Characterization of Silicon <i>V. V. Voronkov, G. I. Voronkova, A. V. Batunina and R. Falster</i>	25
Detection of Vacancy Distributions by Decoration with Hydrogen <i>R. Job, F. Niedernostheide, H. Schulze and H. Schulze</i>	35
Probing the Behaviors of Point Defects in Silicon and Germanium Using Isotope Superlattices <i>M. Uematsu, M. Naganawa, Y. Shimizu, K. M. Itoh, K. Sawano, Y. Shiraki and E. E. Haller</i>	51
Electrical Characterization of Deep-Lying Donor Layers Created by Proton Implantation and Subsequent Annealing in N-Type Float Zone and Czochralski Silicon <i>V. Komarnitskyy and P. Hazdra</i>	55
Comparison of Evaluation Criteria for Efficient Gettering of Cu and Ni in Silicon Wafers <i>D. Kot, G. Kissinger, A. Sattler and W. von Ammon</i>	67
Copper Decoration and Etching for Delineation of Crystal Defects in Thick SOI <i>H. Idrisi, S. Riedmüller, J. Zoller and B. Kolbesen</i>	79

Characterization of Structural Defects in Silicon and SOI Wafers by Means of Laser Scattering Tomography	91
<i>V. A. Monier, L. Capello, O. Kononchuk and B. Pichaud</i>	

## **Chapter 2** **Surfaces, Interfaces and Thin Films and Devices**

Considerable Improvement of Depth Resolution in Auger Sputter Depth Profiling of Polycrystalline Thin Films Using In-situ Sample Preparation Methods	103
<i>U. Scheithauer</i>	
Semiconductor Thin Film Characterization with ac Surface Photo Voltage	119
<i>E. Tsidilkovski</i>	
Comparison of Silicon Surface Preparation Methods for Measurement of Minority Carrier Lifetime using the Microwave Photo-conductive Decay ( $\mu$ -PCD) coupled with Continuous Corona Charge (Charge-PCD)	129
<i>T. Pavelka, A. Pap, P. Kenesei, M. Varga, F. Novinics, M. Tallian, G. Borionetti, G. Guaglio, M. Pfeffer and E. R. Don</i>	
The Application of Differential Hall Effect Continuous Anodic Oxidation Technique for Ultra Shallow Structures	139
<i>S. Prussin and J. Reyes</i>	
A DLTS study of Pt/ $\text{Al}_2\text{O}_3/\text{In}_x\text{Ga}_{1-x}\text{As$ Capacitors	151
<i>E. R. Simoen, G. Brammertz, J. Penaud, C. Merckling, H. C. Lin, W. Wang and M. Meuris</i>	
Charge Trapping in HfYO <sub>x</sub> Gate Dielectrics on Strained-Si	163
<i>B. Majhi, C. Mahata and C. Maiti</i>	
Surface Generation-Recombination Processes of Gate and STI Oxide Interfaces Responsible For Junction Leakage on SOI	169
<i>Y. Liu and V. Koldyaev</i>	
Quantitative Estimation of Strained Si/SiGe Hetero Structure Using C-V Characteristics of Strained Si MOS Capacitors	179
<i>M. Inagaki and S. Matsumoto</i>	
Probing the Strain States in Nanopatterned Strained SOI	187
<i>O. Moutanabbir, M. Reiche, A. Hänel, W. Erfurth, F. Naumann, M. Petzold and U. Goesele</i>	

Two-dimensional Chemical Delineation of Junction Profile with High Spatial Resolution and Application in Failure Analysis in 65nm Technology Node <i>B. Liu, Y. Hua, Z. Mo and N. Adrian</i>	195
Controlling Copper ECD Processes by Early Fault Detection and Diagnosis Using In-situ Electrochemical Sensor Coupled with Pattern Recognition Chemometrics <i>A. Jaworski, H. Wikiel and K. Wikiel</i>	199
Studies on Galvanic Corrosion on Floating and Grounded Bondpads in Wafer Fabrication <i>Y. Hua, L. Ping, N. R. Rao and T. Qinghua</i>	219
Investigation on Particle Generation Mechanism during Dichlorosilane-Based WSi Deposition Process <i>M. Oh, J. Kim, J. Kim, J. Yang, S. Lee and T. Kim</i>	225
3-D Modeling of Wafer Topography's Effect on Chemical Mechanical Polishing Process <i>L. Wu and C. Yan</i>	233
Drain Leakage Current Evaluation in the Diamond SOI nMOSFET at High Temperatures <i>M. Bellodi and S. Gimenez</i>	243
Poly Si TFT on Microsheet <i>S. Won</i>	255
The Characterization of Bottom-gate Thin Film Transistors adapted Nanocrystalline Silicon as Active Layer by Catalytic CVD at Low Temperature <i>Y. Lee, K. Lee, J. Hwang, K. No, K. Yoon, S. Yang, S. Won, J. Sok, K. Park and W. Hong</i>	259
Characterization of SiGe/Si Quantum Dot Grown by using APRPCVD <i>T. Kim, M. Jeong, N. Mun, Y. Kil, J. Kim, T. Jeong, S. Kang, S. Kim, C. Choi and K. Shim</i>	263
Characterization and Modeling of the Electrical Behavior and Threshold Voltage of the Nanocrystalline GZO Delta-doped ZnO TFTs <i>S. Hsiao, K. Liu, H. Chiang, L. Su, L. Peng and J. Huang</i>	271
Confinement Effect on CdTe <i>C. Frausto Reyes, J. R. Molina-Contreras, H. Pérez Ladrón de Guevara, C. Medel Ruiz and Y. López Álvarez</i>	277

The Technique to Characterize Irreversible Domain Motion in Ferroelectric Thin Films in a Large Time Scale <i>A. Jiang</i>	283
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### Chapter 3 ANNA I (Joint Research and Networking Activities)

Characterisation of High-k Containing Nanolayers by Reference-Free X-Ray Fluorescence Analysis with Synchrotron Radiation <i>M. Kolbe, B. Beckhoff, M. Krumrey, M. Reading, J. van den Berg, T. Conard and S. De Gendt</i>	293
Si Wafer Analysis of Light Elements by TXRF <i>S. Sasamori, F. Meirer, N. Zoeger, C. Streli, P. Kregsamer, S. Smolek, C. Mantler and P. Wobrauscheck</i>	301
Assessing Various Analytical Techniques with Different Lateral Resolution by Investigating Spin-coated Inorganic Contamination on Si Wafer Surfaces <i>B. Beckhoff, A. Nutsch, R. Altmann, G. Borionetti, C. Pello, M. Polignano, D. Codegoni, S. Grasso, E. Cazzini, M. Bersani, S. Gennaro, M. Kolbe, M. Mueller, P. Kregsamer and F. Posch</i>	311
Comparability of TXRF Systems at Different Laboratories <i>A. Nutsch, B. Beckhoff, R. Altmann, M. Polignano, E. Cazzini, D. Codegoni, G. Borionetti, M. Kolbe, M. Mueller, C. Mantler, C. Streli and P. Kregsamer</i>	325
Revealing Copper Contamination in Silicon after Low Temperature Treatments <i>M. Polignano, J. Brivio, D. Codegoni, S. Grasso, R. Altmann, A. Nutsch and G. Pavia</i>	337
High Depth Resolution Depth Profile Analysis of Ultra Thin High-k Hf Based Films using MEIS Compared with XTEM, XRF, SE and XPS <i>J. van den Berg, M. Reading, A. Parisini, M. Kolbe, B. Beckhoff, S. Ladas, M. Fried, P. Petrik, P. Bailey, T. Noakes, T. Conard and S. De Gendt</i>	349
Comparison of Electrical Measurements with Structural Analysis of Thin High-k Hafnium-based Films <i>E. Hourdakis, M. Theodoropoulou, A. Nassiopoulou, A. Parisini, M. Reading, J. van den Berg, T. Conard and S. Degendt</i>	363

Preparation and Characterization of Nanocrystals using Ellipsometry and X-ray Diffraction	373
<i>P. Petrik, S. Milita, G. Pucker, A. Nassiopoulou, J. van den Berg, M. Reading, M. Fried, T. Lohner, M. Theodoropoulou, S. Gardelis, M. Barozzi, M. Ghulinyan, A. Lui, L. Vanzetti and A. Picciotto</i>	
Effect of High-temperature Annealing on Evaporated Silicon Oxide Films: A Spectroscopic Ellipsometry Study	379
<i>A. Szekeres, E. Vlaikova, T. Lohner, P. Petrik, A. Cziraki, S. Zlobin and P. Shepeliovici</i>	
Improved TEM Sample Preparation by Low Energy FIB for Strain Analysis by Convergent Beam Electron Diffraction	385
<i>R. Balboni, G. Borionetti, L. Moiraghi, G. Vaccari, M. Polignano, G. Carnevale, F. Cazzaniga, I. Mica and F. Sammiceli</i>	
A Study of the Morphology of 3C-SiC Layers Grown at Different C/Si Ratios	397
<i>G. Attolini, B. E. Watts, M. Bosi, F. Rossi and F. Riesz</i>	
Effect of Nanodiamond Particles Incorporation in Hydroxyapatite Coatings	403
<i>E. Pecheva, L. Pramatarova, A. Toth, T. Hikov, D. Fingarova, S. Stavrev, E. Jacob and L. Vanzetti</i>	
Atomistic Modeling of Junction Formation: Tools for Physics Understanding and Process Optimization	411
<i>L. Pelaz, M. Aboy, L. Marques, P. Lopez and I. Santos</i>	

#### **Chapter 4 ANNA II (Transnational Access)**

Investigations of the Surface Chemical Composition and Atomic Structure of ex-situ Sulfur Passivated Ge(100)	421
<i>C. Fleischmann, S. Sioncke, K. Schouteden, K. Paredis, B. Beckhoff, M. Mueller, M. Kolbe, M. Meuris, C. Van Haesendonck, K. Temst and A. Vantomme</i>	
A Comparison Between Self-assembled Monolayers on Gold and Germanium Employing Grazing Incidence X-ray Absorption Spectrometry GIXRF-NEXAFS	433
<i>M. Lommel, F. Reinhardt, P. Hoenicke, M. Kolbe, M. Mueller, B. Beckhoff and B. Kolbesen</i>	

Probing Patterned Wafer Structures by Means of Grazing Incidence X-ray Fluorescence Analysis <i>J. Osan, F. Reinhardt, B. Beckhoff, A. Pap and S. Torok</i>	441
Detection of Acidic Substances of H-X Type in Clean Room Air <i>J. Kames, A. Leibold, A. Nutsch and M. Otto</i>	453
Author Index	463